



NexGen Vertical GaN 700 V and 1200 V Devices Sample Request

NexGen Vertical GaN junction field effect transistors (JFETs) are made from gallium nitride (GaN). They use a vertical GaN-on-GaN device structure which delivers high switching frequencies at blocking voltages from 700V to 1200V and higher. These devices have very low conduction and switching losses enabling systems with higher efficiencies. Thus, making it an ideal power semiconductor for applications from LED Lighting and Computing to Data Centers and Electric Vehicles. The world's first [700V and 1200V Vertical GaN semiconductors](#) are available to customers!

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